

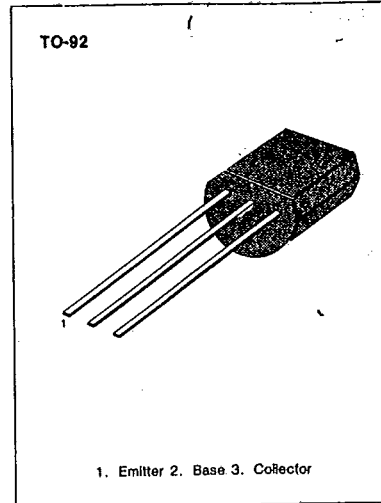
MPSA20**NPN EPITAXIAL SILICON TRANSISTOR****AMPLIFIER TRANSISTOR**

- Collector-Emitter Voltage: $V_{CE0} = 40V$
- Collector Dissipation: $P_C (max) = 625mW$

ABSOLUTE MAXIMUM RATINGS ($T_a = 25^\circ C$)

Characteristic	Symbol	Rating	Unit
Collector-Emitter Voltage	V_{CE0}	40	V
Emitter-Base Voltage	V_{EBO}	4	V
Collector Current	I_C	100	mA
Collector Dissipation	P_C	625	mW
Junction Temperature	T_J	150	$^\circ C$
Storage Temperature	T_{stg}	-55 ~ 150	$^\circ C$

- Refer to MPSA10 for graphs

**3****ELECTRICAL CHARACTERISTICS ($T_a = 25^\circ C$)**

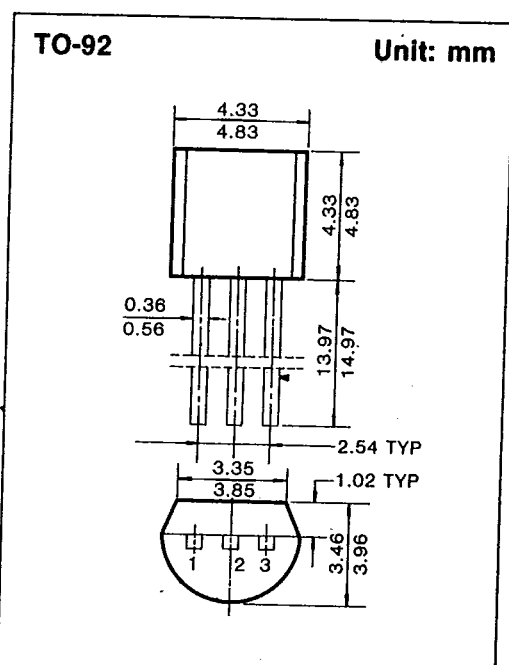
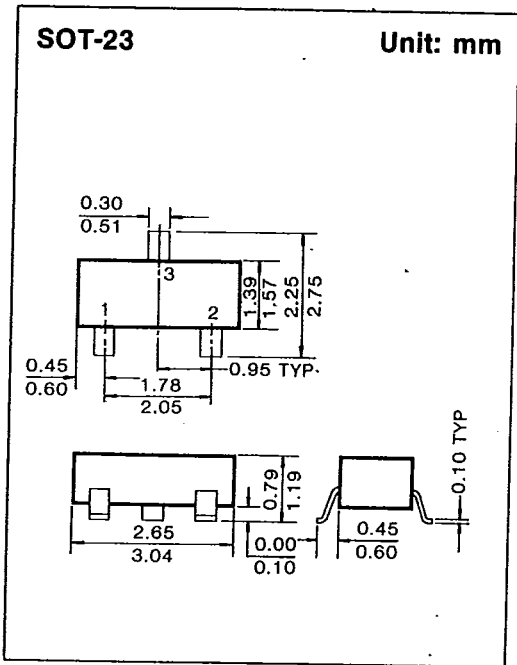
Characteristic	Symbol	Test Conditions	Min	Typ	Max	Unit
*Collector-Emitter Breakdown Voltage	BV_{CE0}	$I_C = 1mA, I_B = 0$	40			V
Emitter-Base Breakdown Voltage	BV_{EBO}	$I_E = 100\mu A, I_C = 0$	4			V
Collector Cut-off Current	I_{CBO}	$V_{CB} = 30V, I_E = 0$			100	nA
*DC Current Gain	h_{FE}	$I_C = 5mA, V_{CE} = 10V$	40		400	
*Current Gain Bandwidth Product	f_T	$I_C = 5mA, V_{CE} = 10V$ $f = 100MHz$	125			MHz
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	$I_C = 10mA, I_B = 1mA$			0.25	V
Output Capacitance	C_{ob}	$V_{CB} = 10V, I_E = 0$ $f = 100KHz$			4	pF

- * Pulse Test: Pulse Width $\leq 300\mu s$, Duty Cycle $\leq 2\%$

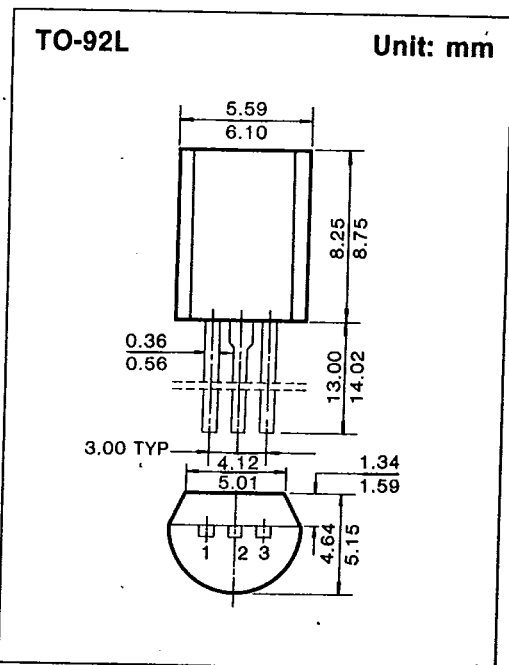
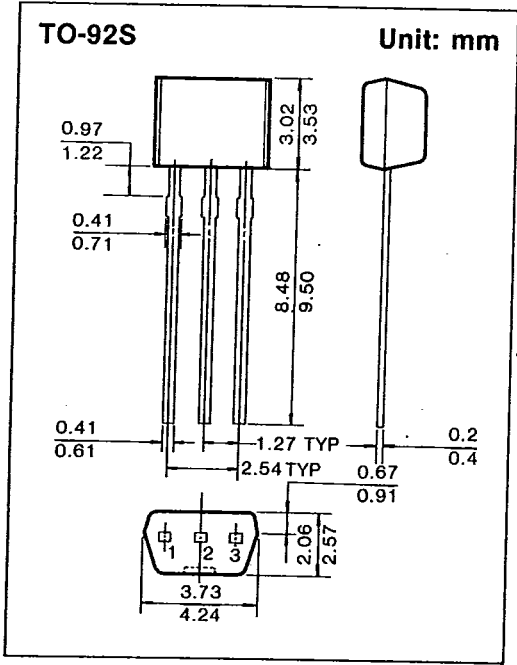


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PACKAGE DIMENSIONS

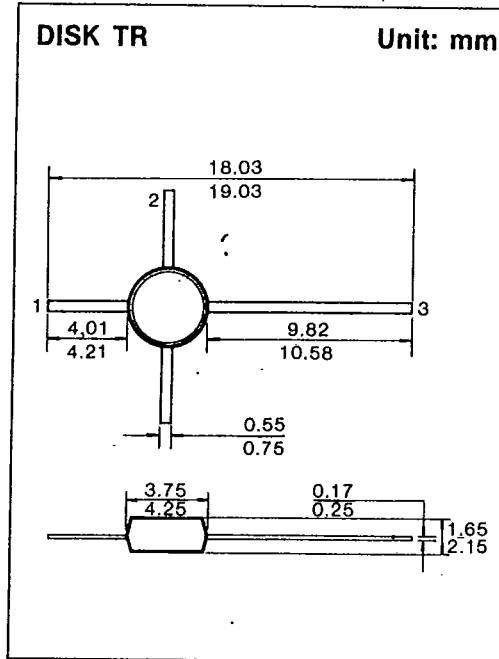
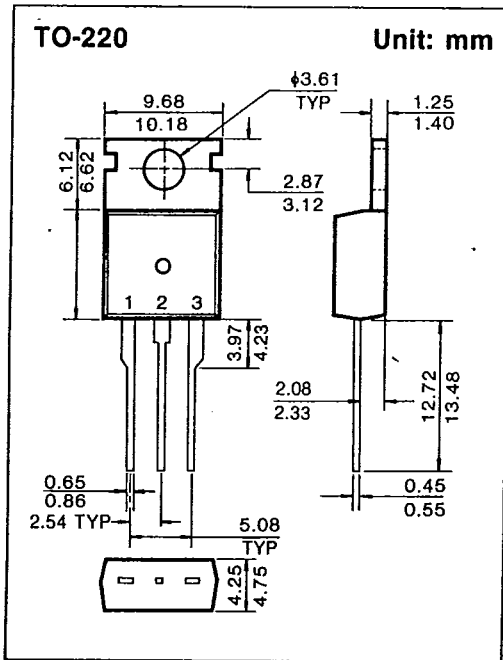
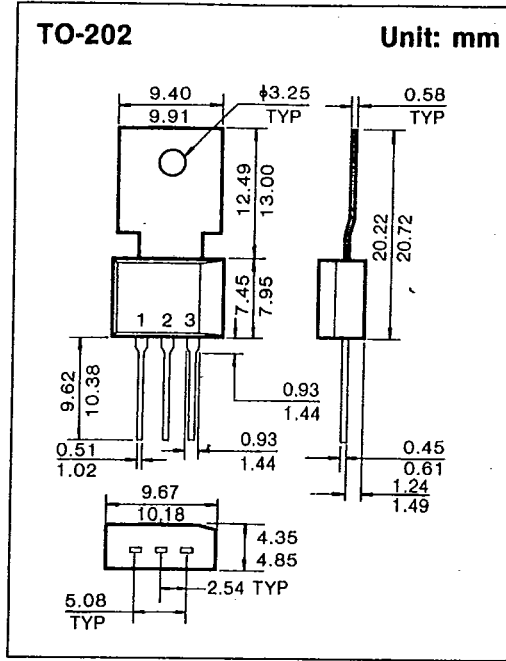
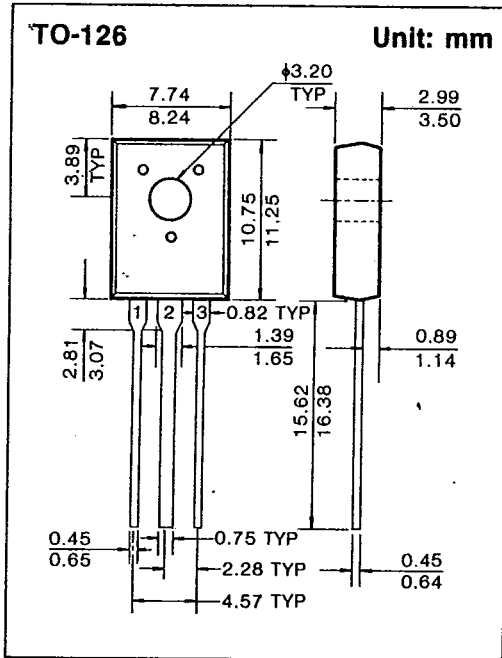


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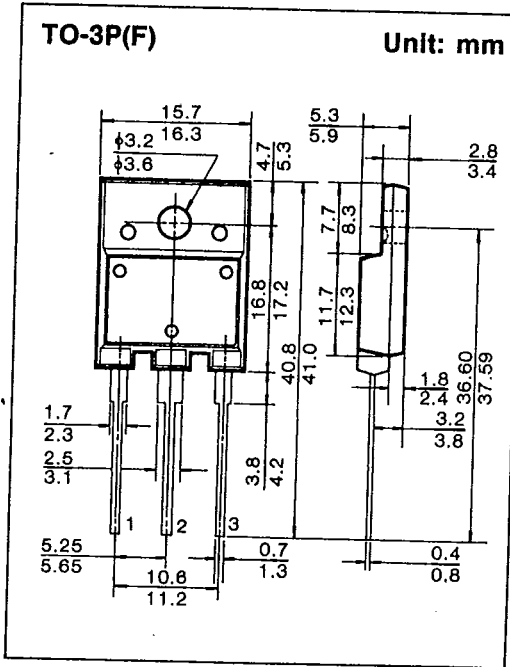
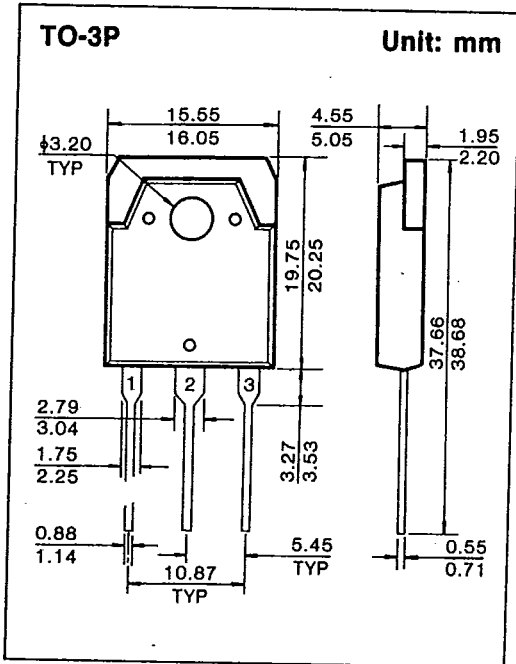
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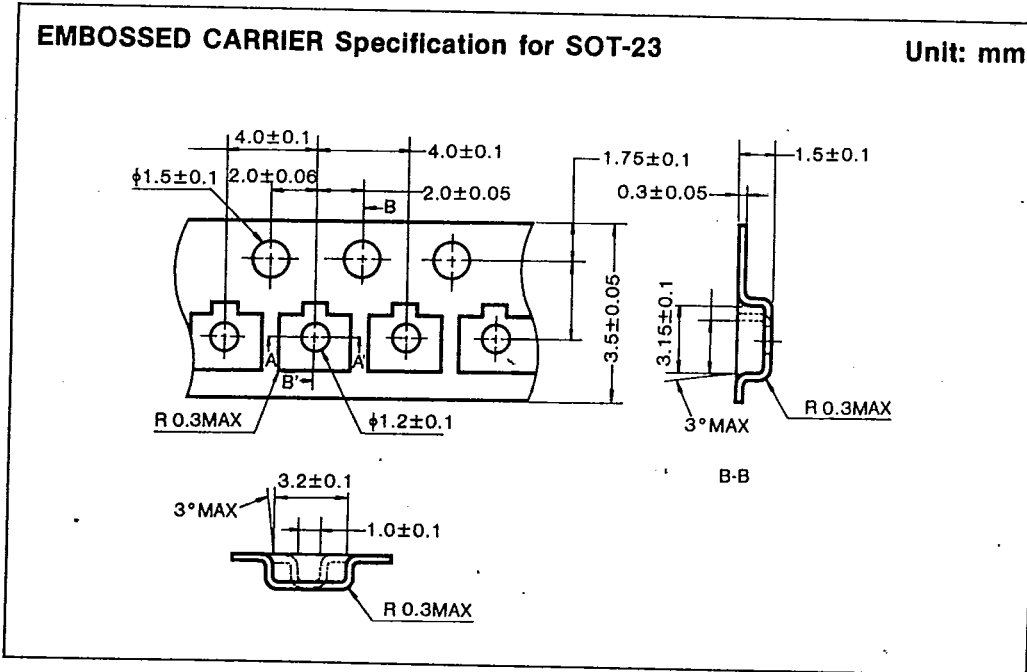


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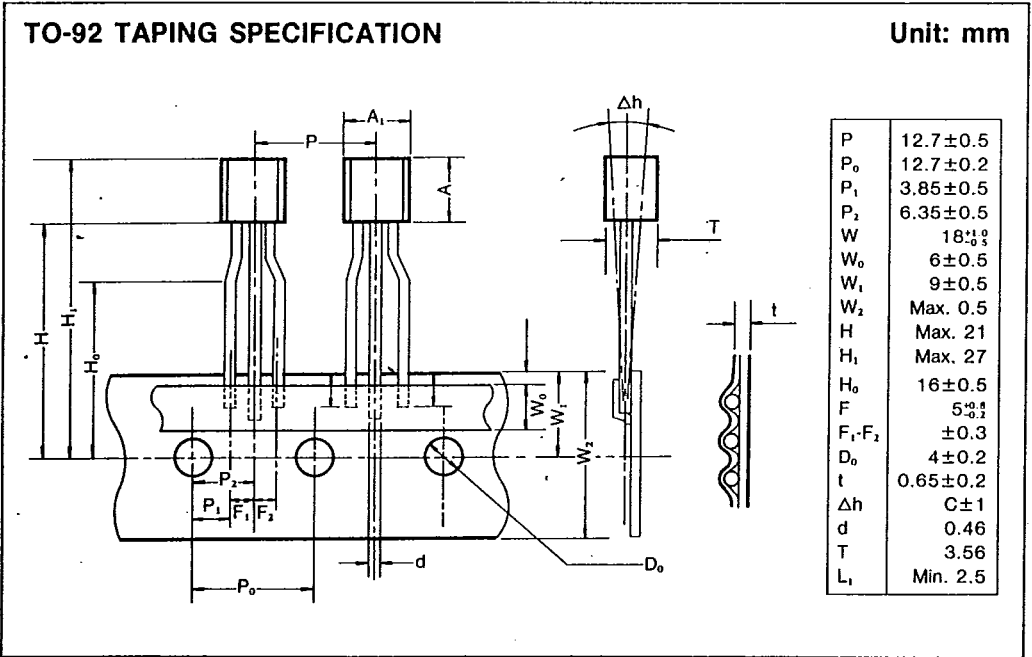
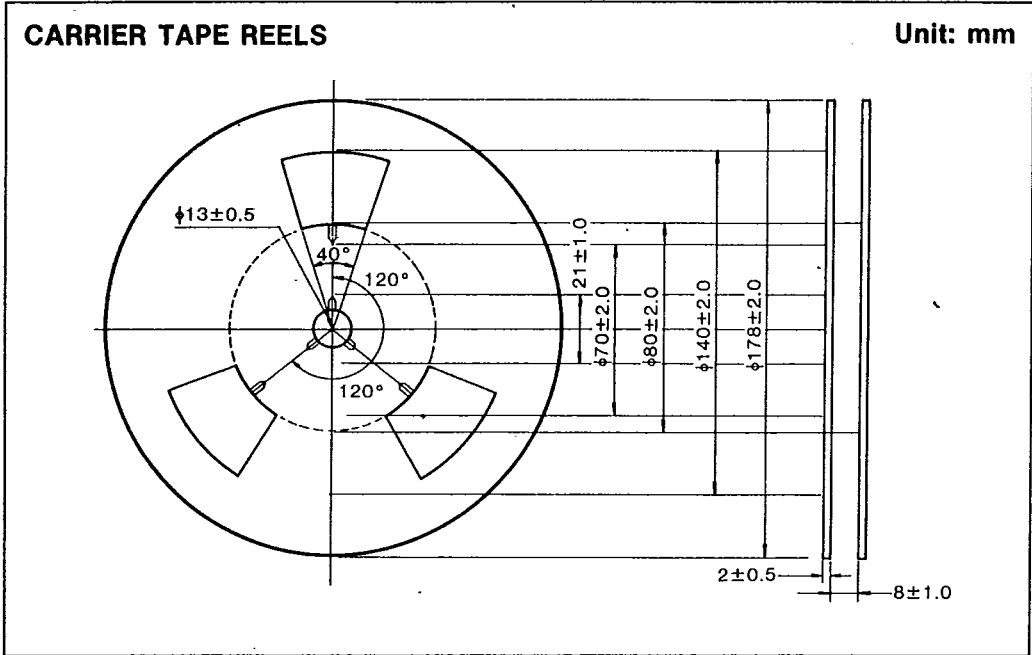


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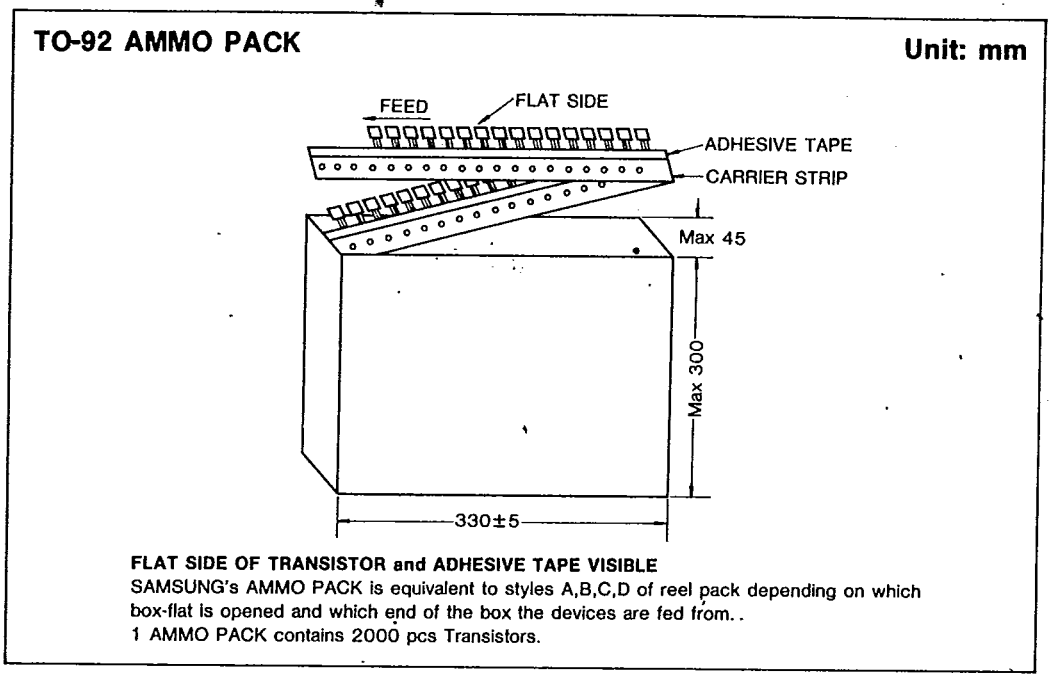
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PACKAGE DIMENSIONS

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